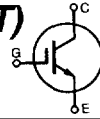
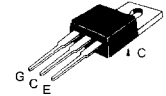


NPT Insulated Gate Bipolar Transistors (IGBT)

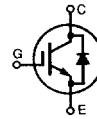


D series (SCSOA)

Type	V_{CES}	I_C	I_C	$V_{CE(sat)}$	C_{ies}	E_{off}	t_{fi}	t_{sc}	R_{thJC}	P_C	Fig. No.	Package style
$T_{JM} = 150^\circ\text{C}$ New	V	$T_C = 25^\circ\text{C}$ A	$T_C = 90^\circ\text{C}$ A	V	pF	typ. 125°C mJ	typ. 25°C ns	μs	max. K/W	max. W		Outlines on page 51/52 G = Gate, E = Emitter, C = Collector
IXDP 20N60B	600	31	21	2.0	800	0.55	55	10	0.9	135	3	Fig. 3 TO-220AB Weight = 4 g
IXDP 35N60B		58	40	2.0	1600	1.1	70	10	0.5	250	3	
IXDH 35N60B											6	
IXDA 20N120A	1200	30	21	2.5	1000	1.5	40	10	0.63	200	5a	Fig. 5a TO-263AA Weight = 2 g
IXDH 20N120		39	25	2.0	1000	2.0	70	10	0.63	200	6	
IXDH 30N120		60	35	2.0	1650	3.0	70	10	0.42	300	6	
IXDN 75N120A		120	70	2.5	5100	2.5	70	10	0.2	630	12	

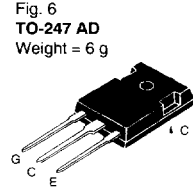
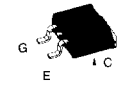


NPT Insulated Gate Bipolar Transistors (IGBT) with Diode

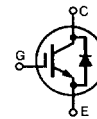


D series (SCSOA)

Type	V_{CES}	I_C	I_C	$V_{CE(sat)}$	C_{ies}	E_{off}	t_{fi}	t_{sc}	R_{thJC}	P_C	Fig. No.	Package style
$T_{JM} = 150^\circ\text{C}$ New	V	$T_C = 25^\circ\text{C}$ A	$T_C = 90^\circ\text{C}$ A	V	pF	typ. 25°C mJ	typ. 25°C ns	μs	max. K/W	max. W		Outlines on page 51/52 G = Gate, E = Emitter, C = Collector
IXDP 20N60BD1	600	31	21	2.0	800	0.55	55	10	0.9	135	3	Fig. 6 TO-247 AD Weight = 6 g
IXDH 35N60BD1		58	40	2.0	1600	1.1	70	10	0.5	250	6	
IXDH 20N120AU1	1200	30	21	2.5	1000	1.5	40	10	0.63	200	6	Fig. 10 TO-268 Weight = 4 g
IXDH 20N120D1		39	25	2.0	1000	2.0	70	10	0.63	200	6	
IXDH 30N120AU1		50	31	2.5	1650	2.4	50	10	0.42	300	6	
IXDT 30N120AU1											10	
IXDH 30N120D1		60	35	2.0	1650	3.0	70	10	0.42	300	6	
IXDN 50N120AU1 ①		70	44	2.5	3300	4.8	70	10	0.35	350	12	
IXDN 55N120AU1 ①		85	52						0.28	450	12	
IXDN 55N120D1 ①	100	60	2.0	3300	5.5	70	10	0.28	450	12		

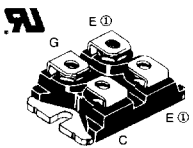


Insulated Gate Bipolar Transistors (BIMOSFET)



B series Fast High Voltage Switches

Type	V_{CES}	I_C	I_C	$V_{CE(sat)}$	C_{ies}	C_{res}	E_{off}	t_{fi}	R_{thJC}	P_C	Fig. No.	Package style
$T_{JM} = 150^\circ\text{C}$ New	V	$T_C = 25^\circ\text{C}$ A	$T_C = 90^\circ\text{C}$ A	V	pF	pf	typ. 125°C mJ	typ. 125°C ns	max. K/W	max. 25°C W		Outlines on page 51/52 G = Gate, E = Emitter, C = Collector
IXBH 9N140	1400	9	5	7.0	550	5	0.29	40	1.25	100	6	Fig. 12 SOT-227B miniBLOC Weight = 30 g
IXBH 9N160		1600										
IXBH 15N140	1400	15	9	7.0	1200	11	0.45	40	0.83	150	6	Fig. 12 SOT-227B miniBLOC Weight = 30 g
IXBH 15N160		1600										
IXBH 20N140	1400	20	12	7.0	2000	20	1.5	40	0.62	200	6	Fig. 12 SOT-227B miniBLOC Weight = 30 g
IXBH 20N160		1600										
IXBH 40N140	1400	33	20	7.0	3300	30	1.3	35	0.35	350	6	Fig. 12 SOT-227B miniBLOC Weight = 30 g
IXBH 40N160		1600										



IXBH data preliminary